

KSC1623**NPN EPITAXIAL SILICON TRANSISTOR**

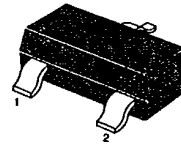
**LOW FREQUENCY AMPLIFIER
HIGH FREQUENCY OSC**

• Complement to KSA812

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	100	mA
Collector Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55~150	°C

SOT-23



1. Base 2. Emitter 3. Collector

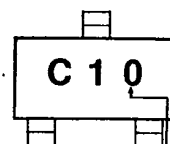
ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} =60V, I _E =0			0.1	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} =5V, I _C =0			0.1	μA
DC Current Gain	h _{FE}	V _{CE} =6V, I _C =1mA	90	200	600	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA		0.15	0.3	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA		0.86	1.0	V
Base-Emitter On Voltage	V _{BE(on)}	I _C =1mA, V _{CE} =6V	0.55	0.62	0.65	V
Current Gain-Bandwidth Product	f _T	I _E =-10mA, V _{CE} =6V		250		MHz
Output Capacitance	C _{ob}	V _{CB} =6V, I _E =0 f=1MHz		3		pF

h_{FE} CLASSIFICATION

Classification	O	Y	G	L
h _{FE}	90-180	135-270	200-400	300-600

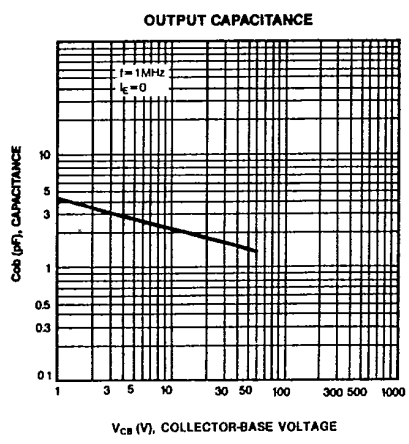
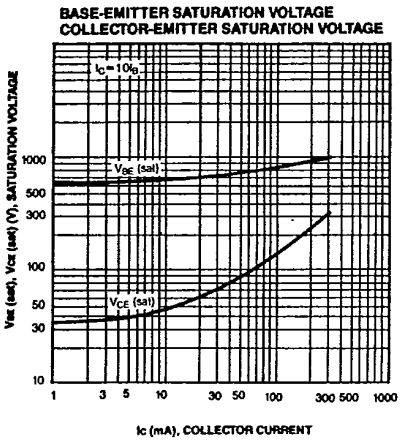
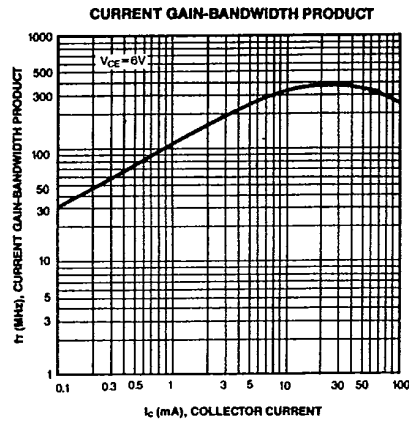
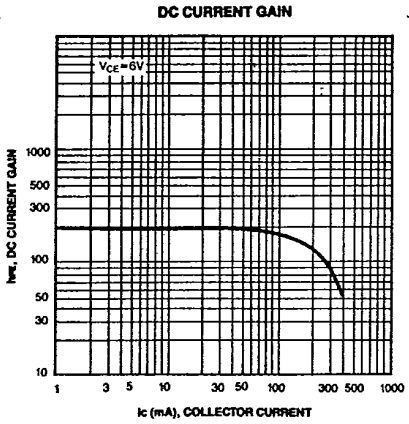
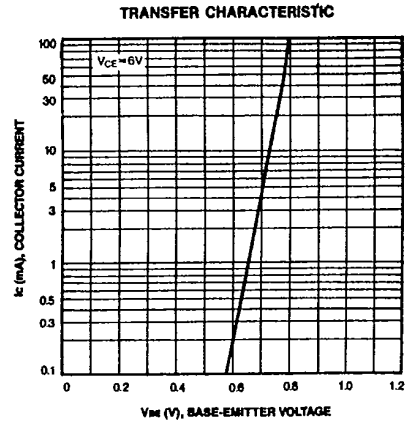
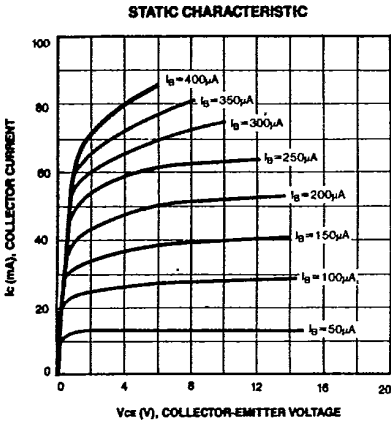
Marking

h_{FE} grade

KSC1623

NPN EPITAXIAL SILICON TRANSISTOR

T-31-15



3